

L Number	Hits	Search Text	DB	Time stamp
-	455704	diode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 12:56
-	23957	Schottky	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 12:56
-	58252	MOS adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 12:57
-	153048	silicon near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 12:57
-	45236	silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 12:59
-	156	diode and Schottky and (MOS adj transistor) and (silicon near5 substrate) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 13:01
-	3	(titanium tungsten cobalt platinum) near5 silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 13:01
-	17605	(titanium tungsten cobalt platinum) near5 silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 13:01
-	98	diode and Schottky and (MOS adj transistor) and (silicon near5 substrate) and ((titanium tungsten cobalt platinum) near5 silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 13:08
-	3	(diode and Schottky and (MOS adj transistor) and (silicon near5 substrate) and ((titanium tungsten cobalt platinum) near5 silicide)) and ((IC (integrated adj circuit)) near5 (card module))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 13:09
-	74	(diode and Schottky and (MOS adj transistor) and (silicon near5 substrate) and ((titanium tungsten cobalt platinum) near5 silicide)) and (IC (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/21 13:10